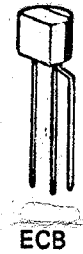


MICRO ELECTRONICS CRO

BC 368, 9

EPITAXIAL TRANSISTORS

TO-92B



BC 368 (NPN) and BC 369 (PNP) are complementary silicon epitaxial transistors for audio frequency application.

ABSOLUTE MAXIMUM RATINGS

Collector Current-Continuous		1A
Collector-Emitter Voltage	V_{CEO}	20V
Emitter-Base Voltage	V_{EBO}	5V
Total Power Dissipation	P_{tot}	0.8W
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 to 150°C

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BV _{CE} S	25			V	$I_C=1mA$ $V_{BE}=0$
Collector-Emitter Breakdown Voltage	BV _{CE0} *	20			V	$I_C=10mA$ $I_B=0$
Emitter-Base Breakdown Voltage	BV _{EB0}	5			V	$I_E=0.1mA$ $I_C=0$
Collector Cutoff Current	I_{CBO}			10	μA	$I_E=0$ $V_{CB}=25V$
Collector Cutoff Current	I_{CBO}			1	mA	$I_B=0$ $V_{CB}=25V$ $T_A=150^\circ C$
Emitter Cutoff Current	I_{EBO}			10	μA	$I_C=0$ $V_{EB}=5V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$ *			0.5	V	$I_C=1A$ $I_B=0.1A$
Base-Emitter Voltage	V_{BE}			0.6	V	$I_C=5mA$ $V_{CE}=10V$
Base-Emitter Voltage	V_{BE}^*			1	V	$I_C=1A$ $V_{CE}=1V$
D.C. Current Gain	HFE	50				$I_C=5mA$ $V_{CE}=10V$
D.C. Current Gain	HFE*	85		375		$I_C=500mA$ $V_{CE}=1V$
D.C. Current Gain	HFE*	60				$I_C=1A$ $V_{CE}=1V$
Current Gain-Bandwidth Product	fT		65		MHz	$I_C=10mA$ $V_{CE}=5V$ $f=20MHz$
Output Capacitance	Cob			30	PF	$V_{CB}=10V$

* Pulse Test : Pulse Width = 300 μ S, Duty Cycle = 1%.

MICRO ELECTRONICS LTD. 美科有限公司

38 Hung To Road, Kwun Tong, Kowloon, Hong Kong. Cable: Microtron, Hong Kong. Telex: 43510 Micro Hx.
P.O. Box 9477, Kwun Tong. Tel: 3-430181-6, 3-893363, 3-892423, 3-898224

FAX: 3-410321